	Application No.	Applicant(s)
Notice of Allowability	10/663,779	KAMIGAKI ET AL.
	Examiner	Art Unit
	Kevin Quinto	2826
The MAILING DATE of this communication apper All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313  1. This communication is responsive to 24 September 2004.	ears on the cover sheet with (OR REMAINS) CLOSED in the or other appropriate communi IGHTS. This application is sub	the correspondence address nis application. If not included cation will be mailed in due course. THIS
2. ☑ The allowed claim(s) is/are <u>1 and 15-19</u> .		NATURE
3. The drawings filed on 17 September 2003 are accepted by	the Examiner.	FRVISORY PATENT EXAMINER  CHNOLOGY CENTER 2800
4. ☐ Acknowledgment is made of a claim for foreign priority un  a) ☐ All b) ☐ Some* c) ☐ None of the:		(f). 2800
1. Certified copies of the priority documents have been received.		
<ul> <li>2.  Certified copies of the priority documents have been received in Application No. <u>09/660,923</u>.</li> <li>3.  Copies of the certified copies of the priority documents have been received in this national stage application from the</li> </ul>		
International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:		
Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file a ENT of this application.	reply complying with the requirements
5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.		
6. CORRECTED DRAWINGS (as "replacement sheets") must  (a) including changes required by the Notice of Draftspers  1) hereto or 2) to Paper No./Mail Date  (b) including changes required by the attached Examiner's Paper No./Mail Date  ldentifying indicia such as the application number (see 37 CFR 1. each.sheet. Replacement sheet(s) should be labeled as such in the	on's Patent Drawing Review (  Amendment / Comment or in  84(c)) should be written on the o	the Office action of
7. DEPOSIT OF and/or INFORMATION about the depose attached Examiner's comment regarding REQUIREMENT For the REGISTANCE FOR THE	sit of BIOLOGICAL MATER FOR THE DEPOSIT OF BIOLO	IAL must be submitted. Note the DGICAL MATERIAL.
Attachment(s)  1. ☑ Notice of References Cited (PTO-892)  2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)	5. ☐ Notice of Inform	mal Patent Application (PTO-152)
	Paper No./Ma	
<ol> <li>Information Disclosure Statements (PTO-1449 or PTO/SB/08</li> <li>Paper No./Mail Date</li> </ol>		
Examiner's Comment Regarding Requirement for Deposit  of Rightsian Material		atement of Reasons for Allowance
of Biological Material	9.	
•		
·		



Application/Control Number: 10/663,779

Art Unit: 2826

## **EXAMINER'S AMENDMENT**

1. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.

Authorization for this examiner's amendment was given in a telephone interview with Shrinath Malur (Reg. No. 34,663) on December 10, 2004.

The application has been amended as follows:

- a. In claim 15, line 8, change "perpendicular said first direction" to -- , perpendicular to said first direction--.
- b. In claim 15, line 9, change "cell" to --cells--.
- c. In claim 15, line 26, change "switch g ate" to **--switch gate--**.
- d. In claim 15, lines 29-30, delete "which is neighboring tone nonvolatile memory cell".
- 2. Claims 1 and 15-19 are allowed.
- 3. The following is an examiner's statement of reasons for allowance: the examiner is unaware of any prior art which suggests a nonvolatile memory cell having a memory transistor (having a gate insulating film with discrete traps) formed between two switch transistors which are formed between two impurity region lines that form the source and bit lines such that the gate electrodes of the switch transistors extend along the source

Application/Control Number: 10/663,779

Art Unit: 2826

and bit lines thereby allowing the continuous formation of channels (of the memory and switch transistors) between the two impurity region lines.

4. Hayashi et al. (USPN 4,868,632) discloses a memory transistor. Although Hayashi discusses the trap potential and its affect on memory retention, there is no disclosure of additional switch transistors on its sides which are between source and bit impurity region lines. Thus Hayashi does not teach the applicant's device.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

## Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kevin Quinto whose telephone number is (571) 272-1920. The examiner can normally be reached on M-F 8AM-5PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

**KVQ**